

Supporting Information

Performance Modulation of Transparent ALD Indium Oxide Films on Flexible Substrates:

Transition between Metal-like Conductor and High Performance Semiconductor States

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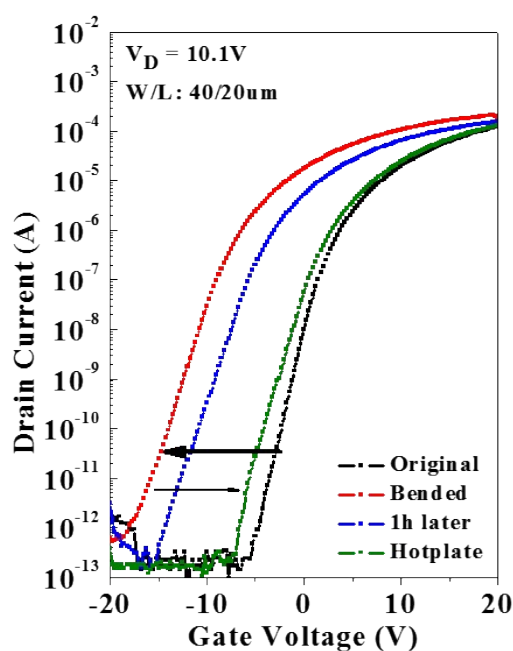


Figure S1. Representative transfer characteristics in the Original state, After Bending, 1 hour after stress removal, and after thermal treatment on a Hotplate (at 200°C for 20 min.), respectively.

	V_{th} [V]	M_{sat} [cm^2/Vs]	S.S. [V/decade]	I_{ON}/I_{OFF}
Original	0.3	9.2	0.96	4.6E+9
Bended	-10.4	7.2	1.5	2.1E+9
1 hour later	-7.0	7.8	1.2	1.4E+9
Hotplate	-0.7	8.9	0.8	1.8E+9

Table S1. Device parameters in the Original state, After Bending, 1 hour after stress removal, and after thermal treatment on a Hotplate (at 200°C for 20 min.), respectively.